



# 低功耗双通道数字隔离器

## 1 特性

- 适用于汽车电子应用
- 下列性能符合 AEC-Q100 标准：
  - 器件温度 1 级：−40°C 至 +125°C 的环境工作温度范围
  - 器件 HBM ESD 分类等级 H3A
  - 器件 CDM ESD 分类等级 C4
- 传播延迟低于 20ns
- 低功耗
- 安全及管理批准：
  - 符合 VDE 标准的 4242V<sub>PK</sub> 隔离，符合 UL 1577 标准的 2.5kVrms 隔离，通过 IEC 60950-1 和 IEC 61010-1 终端设备标准验证的 CSA
- 50kV/μs 瞬态抗扰度典型值
- 工作电压和逻辑电平范围为 3.3V 至 5V

## 2 应用

- 光耦合器替代产品
  - 伺服器控制接口
  - 电机控制
  - 电源
  - 电池组

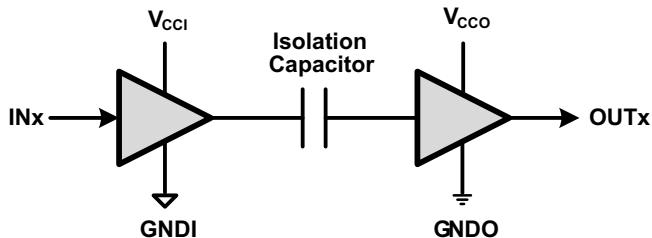
## 3 说明

ISO7421E-Q1 可提供符合 UL 标准、持续时间为 1 分钟的高达 2.5kVrms 的双电隔离。这个数字隔离器在一个双向配置中有两个隔离通道。每个隔离通道都有一个由二氧化硅 ( $\text{SiO}_2$ ) 绝缘隔栅分开的逻辑输入和输出缓冲器。与隔离电源配合使用，这些器件可防止数据总线或者其它电路上的噪声电流进入本地接地并且干扰或损坏敏感电路。

此器件有 TTL 输入阈值并要求两个电源电压，3.3V 或者 5V，或者二者的任意组合。当由一个 3.3V 电源供电时，所有输入为 5V 耐压。

请注意：ISO7421E-Q50 额定信号传输速率高达 50Mbps。由于它们的快速响应时间，在大多数情况下，这些器件还将发送带有更短脉冲宽度的数据。如果需要，设计人员应该增加外部滤波来去除输入脉冲持续时间 < 20ns 的寄生信号。

简化原理图



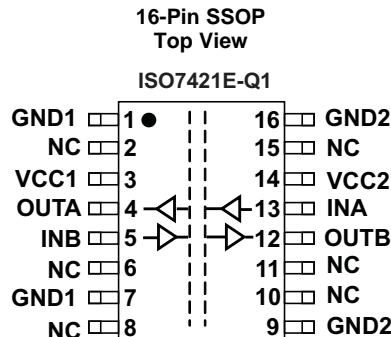
(1) V<sub>CCI</sub> 和 GNDI 分别是输入通道的电源和接地连接引脚。

(2) V<sub>CCO</sub> 和 GNDO 分别是输出通道的电源和接地连接引脚。



本文档旨在为方便起见，提供有关 TI 产品中文版本的信息，以确认产品的概要。有关适用的官方英文版本的最新信息，请访问 [www.ti.com](http://www.ti.com)，其内容始终优先。TI 不保证翻译的准确性和有效性。在实际设计之前，请务必参考最新版本的英文版本。

## 4 Pin Configuration and Functions



**Table 1. Pin Functions**

<b>PIN</b>		<b>I/O</b>	<b>DESCRIPTION</b>
<b>NAME</b>	<b>ISO7421E-Q1</b>		
INA	13	I	Input, channel A
INB	5	–	Input, channel B
GND1	1, 7	–	Ground connection for V <sub>CC1</sub>
GND2	9, 16	O	Ground connection for V <sub>CC2</sub>
OUTA	4	O	Output, channel A
OUTB	12	–	Output, channel B
V <sub>CC1</sub>	14	–	Power supply, V <sub>CC1</sub>
V <sub>CC2</sub>	14	-	Power supply, V <sub>CC2</sub>
NC	2, 6, 8, 10, 11, 15		No Connect Pin

### 4.1 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

## 4.1 Device Function Table

INPUT SIDE V <sub>CC</sub> (V <sub>CC1</sub> ) <sup>(1)</sup>	OUTPUT SIDE V <sub>CC</sub> (V <sub>CC2</sub> ) <sup>(1)</sup>	INPUT (IN) <sup>(1)</sup>	OUTPUT (OUT) <sup>(1)</sup>
PU	PU	H	H
		L	L
		Open	H
PD	PU	X	H

(1) PU = Powered Up ( $V_{CC} \geq 3.15V$ ); PD = Powered Down ( $V_{CC} \leq 2.4V$ ); X = Irrelevant; H = High Level; L = Low Level

## 4.2 Available Options

PRODUCT	RATED T <sub>A</sub>	MARKED AS	ORDERING NUMBER
ISO7421E-Q1	-40°C to 125°C	ISO7421EQ	ISO7421EQDWRQ1

## 5 Absolute Maximum Ratings<sup>(1)</sup>

			VALUE		UNIT
			MIN	MAX	
V <sub>CC</sub>	Supply voltage <sup>(2)</sup> , V <sub>CC1</sub> , V <sub>CC2</sub>		-0.5	6	V
V <sub>I</sub>	Voltage at IN, OUT		-0.5	V <sub>CC</sub> + 0.5 <sup>(3)</sup>	V
I <sub>O</sub>	Output Current			±15	mA
ESD	Electrostatic discharge	Human Body Model	AEC-Q100 Classification Level H3A	All pins	4 kV
		Charged Device Model			1 kV
T <sub>J</sub>	Maximum junction temperature			150	°C

- (1) Stresses beyond those listed under **Absolute Maximum Ratings<sup>(1)</sup>** may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under **Recommended Operating Conditions** is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltage values except differential I/O bus voltages are with respect to network ground terminal and are peak voltage values.
- (3) Maximum voltage must not exceed 6 V. A strongly driven input signal can weakly power the floating V<sub>CC</sub> via an internal protection diode and cause undetermined output.

## 6 Thermal Information

THERMAL METRIC <sup>(1)</sup>	ISO7421E-Q1	UNITS
	DW (16 Pins)	
θ <sub>JA</sub>	Junction-to-ambient thermal resistance	79.9
θ <sub>JCTop</sub>	Junction-to-case (top) thermal resistance	44.6
θ <sub>JB</sub>	Junction-to-board thermal resistance	51.2
Ψ <sub>JT</sub>	Junction-to-top characterization parameter	18.0
Ψ <sub>JB</sub>	Junction-to-board characterization parameter	42.2
θ <sub>JCbot</sub>	Junction-to-case (bottom) thermal resistance	n/a
P <sub>D</sub>	Device power dissipation, V <sub>CC1</sub> = V <sub>CC2</sub> = 5.25 V, T <sub>J</sub> = 150°C, C <sub>L</sub> = 15 pF, Input a 0.5 MHz 50% duty cycle square wave	42 mW

- (1) 有关传统和新热指标的更多信息，请参见应用报告《半导体和 IC 封装热指标》( 文献编号 : [SPRA953](#) )。

## 7 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	TYP	MAX	UNIT
V <sub>CC1</sub> , V <sub>CC2</sub>	Supply voltage - 3.3V Operation	3.15	3.3	3.45	V
	Supply voltage - 5V Operation	4.75	5	5.25	
I <sub>OH</sub>	High-level output current	–4			mA
I <sub>OL</sub>	Low-level output current			4	mA
V <sub>IH</sub>	High-level output voltage	2	V <sub>CC</sub>		V
V <sub>IL</sub>	Low-level output voltage	0	0.8		V
T <sub>A</sub>	Ambient Temperature	-40	125		°C
T <sub>J</sub> <sup>(1)</sup>	Junction temperature	-40	136		°C
1/t <sub>ui</sub>	Signaling rate	0	50		Mbps
t <sub>ui</sub>	Input pulse duration	1			μs

- (1) To maintain the recommended operating conditions for T<sub>J</sub>, see the *Package Thermal Characteristics* table and the *I<sub>cc</sub> Equations* section of this data sheet

## 8 Electrical Characteristics

$V_{CC1}$  and  $V_{CC2}$  at 5 V ± 5%,  $T_A = -40^\circ\text{C}$  to  $125^\circ\text{C}$

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
$V_{OH}$ High-level output voltage	$I_{OH} = -4 \text{ mA}$ ; See <a href="#">图 1</a>	$V_{CC} -0.8$	4.6		V
	$I_{OH} = -20 \mu\text{A}$ ; See <a href="#">图 1</a>	$V_{CC} -0.1$	5		
$V_{OL}$ Low-level output voltage	$I_{OL} = 4 \text{ mA}$ ; See <a href="#">图 1</a>		0.2	0.4	V
	$I_{OL} = 20 \mu\text{A}$ ; See <a href="#">图 1</a>		0	0.1	
$V_{I(HYS)}$ Input threshold voltage hysteresis			400		mV
$I_{IH}$ High-level input current	INx at 0 V or $V_{CC}$			10	$\mu\text{A}$
$I_{IL}$ Low-level input current			-10		$\mu\text{A}$
CMTI Common-mode transient immunity	$V_I = V_{CC}$ or 0 V; See <a href="#">图 3</a>	25	50		kV/ $\mu\text{s}$
<b>SUPPLY CURRENT (All inputs switching with square wave clock signal for dynamic <math>I_{CC}</math> measurement)</b>					
$I_{CC1}$	Supply current for $V_{CC1}$ and $V_{CC2}$	DC to 1 Mbps	DC Input: $V_I = V_{CC}$ or 0 V AC Input: $C_L = 15 \text{ pF}$	2.3	3.6
$I_{CC2}$				2.3	3.6
$I_{CC1}$		10 Mbps		2.9	4.5
$I_{CC2}$				2.9	4.5
$I_{CC1}$		25 Mbps		4.3	6
$I_{CC2}$				4.3	6
$I_{CC1}$		50 Mbps		6	9.1
$I_{CC2}$				6	9.1

## 9 Switching Characteristics

$V_{CC1}$  and  $V_{CC2}$  at 5 V ± 5%,  $T_A = -40^\circ\text{C}$  to  $125^\circ\text{C}$

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
$t_{PLH}, t_{PHL}$ Propagation delay time	See <a href="#">图 1</a>		9	14	ns
PWD <sup>(1)</sup> Pulse width distortion $ t_{PHL} - t_{PLH} $			0.3	3.7	ns
$t_{sk(pp)}$ Part-to-part skew time				4.9	ns
$t_{sk(o)}$ Channel-to-channel output skew time				3.6	ns
$t_r$ Output signal rise time	See <a href="#">图 1</a>		1		ns
$t_f$ Output signal fall time			1		ns
$t_{fs}$ Fail-safe output delay time from input power loss	See <a href="#">图 2</a>		6		$\mu\text{s}$

(1) Also known as pulse skew.

## 10 Electrical Characteristics

$V_{CC1}$  at  $5\text{ V} \pm 5\%$ ,  $V_{CC2}$  at  $3.3\text{ V} \pm 5\%$ ,  $T_A = -40^\circ\text{C}$  to  $105^\circ\text{C}$

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT	
$V_{OH}$	High-level output voltage	$I_{OH} = -4\text{ mA}$ ; See <a href="#">图 1</a>	5-V side	$V_{CC} - 0.8$	4.6		V	
			3.3-V side	$V_{CC} - 0.4$	3			
		$I_{OH} = -20\text{ }\mu\text{A}$ ; See <a href="#">图 1</a>		$V_{CC} - 0.1$	$V_{CC}$			
$V_{OL}$	Low-level output voltage	$I_{OL} = 4\text{ mA}$ ; See <a href="#">图 1</a>			0.2	0.4	V	
		$I_{OL} = 20\text{ }\mu\text{A}$ ; See <a href="#">图 1</a>			0	0.1		
$V_{I(HYS)}$	Input threshold voltage hysteresis			400		mV		
$I_{IH}$	High-level input current	INx at 0 V or $V_{CC}$		10		$\mu\text{A}$		
$I_{IL}$	Low-level input current			-10		$\mu\text{A}$		
CMTI	Common-mode transient immunity	$V_I = V_{CC}$ or 0 V; See <a href="#">图 3</a>		25	40		kV/ $\mu\text{s}$	
<b>SUPPLY CURRENT (All inputs switching with square wave clock signal for dynamic <math>I_{CC}</math> measurement)</b>								
$I_{CC1}$	Supply current for $V_{CC1}$ and $V_{CC2}$	DC to 1 Mbps	DC Input: $V_I = V_{CC}$ or 0 V AC Input: $C_L = 15\text{ pF}$	2.3		3.6		
$I_{CC2}$				1.8		2.8		
$I_{CC1}$		10 Mbps		2.9		4.5		
$I_{CC2}$				2.2		3.2		
$I_{CC1}$		25 Mbps		4.3		6		
$I_{CC2}$				2.8		4.1		
$I_{CC1}$		50 Mbps		6		9.1		
$I_{CC2}$				3.8		5.8		

## 11 Switching Characteristics

$V_{CC1}$  at  $5\text{ V} \pm 5\%$ ,  $V_{CC2}$  at  $3.3\text{ V} \pm 5\%$ ,  $T_A = -40^\circ\text{C}$  to  $125^\circ\text{C}$

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
$t_{PLH}, t_{PHL}$	Propagation delay time	See <a href="#">图 1</a>		10	17		ns
PWD <sup>(1)</sup>	Pulse width distortion $ t_{PHL} - t_{PLH} $			0.5	5.6		ns
$t_{sk(pp)}$	Part-to-part skew time			6.3		ns	
$t_{sk(o)}$	Channel-to-channel output skew time			4		ns	
$t_r$	Output signal rise time	See <a href="#">图 1</a>		2		ns	
$t_f$	Output signal fall time			2		ns	
$t_{fs}$	Fail-safe output delay time from input power loss	See <a href="#">图 2</a>		6		$\mu\text{s}$	

(1) Also known as pulse skew.

## 12 Electrical Characteristics

$V_{CC1}$  at  $3.3\text{ V} \pm 5\%$ ,  $V_{CC2}$  at  $5\text{ V} \pm 5\%$ ,  $T_A = -40^\circ\text{C}$  to  $125^\circ\text{C}$

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT	
$V_{OH}$	High-level output voltage	$I_{OH} = -4\text{ mA}$ ; See <a href="#">图 1</a>	5-V side	$V_{CC} -0.8$	4.6		V	
			3.3-V side	$V_{CC} -0.4$	3			
		$I_{OH} = -20\text{ }\mu\text{A}$ ; See <a href="#">图 1</a>		$V_{CC} -0.1$	$V_{CC}$			
$V_{OL}$	Low-level output voltage	$I_{OL} = 4\text{ mA}$ ; See <a href="#">图 1</a>		0.2 0.4			V	
		$I_{OL} = 20\text{ }\mu\text{A}$ ; See <a href="#">图 1</a>		0 0.1				
$V_{I(HYS)}$	Input threshold voltage hysteresis			400			mV	
$I_{IH}$	High-level input current	INx at 0 V or $V_{CC}$		10			$\mu\text{A}$	
$I_{IL}$	Low-level input current			-10			$\mu\text{A}$	
CMTI	Common-mode transient immunity	$V_I = V_{CC}$ or 0 V; See <a href="#">图 3</a>		25	40		kV/ $\mu\text{s}$	
<b>SUPPLY CURRENT (All inputs switching with square wave clock signal for dynamic <math>I_{CC}</math> measurement)</b>								
$I_{CC1}$	Supply current for $V_{CC1}$ and $V_{CC2}$	DC to 1 Mbps	DC Input: $V_I = V_{CC}$ or 0 V AC Input: $C_L = 15\text{ pF}$	1.8 2.8			mA	
$I_{CC2}$				2.3 3.6				
$I_{CC1}$		10 Mbps		2.2 3.2				
$I_{CC2}$				2.9 4.5				
$I_{CC1}$		25 Mbps		2.8 4.1				
$I_{CC2}$				4.3 6				
$I_{CC1}$		50 Mbps		3.8 5.8				
$I_{CC2}$				6 9.1				

## 13 Switching Characteristics

$V_{CC1}$  at  $3.3\text{ V} \pm 5\%$ ,  $V_{CC2}$  at  $5\text{ V} \pm 5\%$ ,  $T_A = -40^\circ\text{C}$  to  $125^\circ\text{C}$

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
$t_{PLH}, t_{PHL}$		Propagation delay time	See <a href="#">图 1</a>		10 17	ns
PWD <sup>(1)</sup>		Pulse width distortion $ t_{PHL} - t_{PLH} $			0.5 4	ns
$t_{sk(pp)}$		Part-to-part skew time			8.5	ns
$t_{sk(0)}$		Channel-to-channel output skew time			4	ns
$t_r$		Output signal rise time	See <a href="#">图 1</a>		2	ns
$t_f$		Output signal fall time			2	ns
$t_{fs}$		Fail-safe output delay time from input power loss	See <a href="#">图 2</a>		6	$\mu\text{s}$

(1) Also known as pulse skew.

## 14 Electrical Characteristics

$V_{CC1}$  and  $V_{CC2}$  at 3.3 V  $\pm$  5%,  $T_A = -40^\circ\text{C}$  to  $125^\circ\text{C}$

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
$V_{OH}$ High-level output voltage	$I_{OH} = -4 \text{ mA}$ ; See <a href="#">图 1</a>	$V_{CC} -0.4$	3		V	
	$I_{OH} = -20 \mu\text{A}$ ; See <a href="#">图 1</a>	$V_{CC} -0.1$	3.3			
$V_{OL}$ Low-level output voltage	$I_{OL} = 4 \text{ mA}$ ; See <a href="#">图 1</a>		0.2	0.4	V	
	$I_{OL} = 20 \mu\text{A}$ ; See <a href="#">图 1</a>		0	0.1		
$V_{I(HYS)}$ Input threshold voltage hysteresis			400		mV	
$I_{IH}$ High-level input current	INx at 0 V or $V_{CC}$				$\mu\text{A}$	
$I_{IL}$ Low-level input current			-10		$\mu\text{A}$	
CMTI Common-mode transient immunity	$V_I = V_{CC}$ or 0 V; See <a href="#">图 3</a>	25	40		kV/ $\mu\text{s}$	
<b>SUPPLY CURRENT (All inputs switching with square wave clock signal for dynamic <math>I_{CC}</math> measurement)</b>						
$I_{CC1}$	Supply current for $V_{CC1}$ and $V_{CC2}$	DC to 1 Mbps	DC Input: $V_I = V_{CC}$ or 0 V AC Input: $C_L = 15 \text{ pF}$	1.8	2.8	mA
$I_{CC2}$				1.8	2.8	
$I_{CC1}$		10 Mbps		2.2	3.2	
$I_{CC2}$				2.2	3.2	
$I_{CC1}$		25 Mbps		2.8	4.1	
$I_{CC2}$				2.8	4.1	
$I_{CC1}$		50 Mbps		3.8	5.8	
$I_{CC2}$				3.8	5.8	

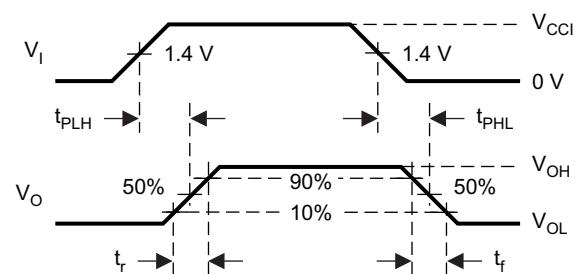
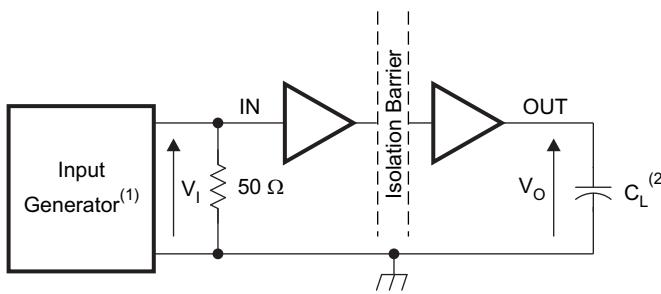
## 15 Switching Characteristics

$V_{CC1}$  and  $V_{CC2}$  at 3.3 V  $\pm$  5%,  $T_A = -40^\circ\text{C}$  to  $125^\circ\text{C}$

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
$t_{PLH}, t_{PHL}$ Propagation delay time	See <a href="#">图 1</a>		12	20	ns
PWD <sup>(1)</sup> Pulse width distortion $ t_{PHL} - t_{PLH} $			1	5	ns
$t_{sk(pp)}$ Part-to-part skew time				6.8	ns
$t_{sk(o)}$ Channel-to-channel output skew time				5.5	ns
$t_r$ Output signal rise time	See <a href="#">图 1</a>		2		ns
$t_f$ Output signal fall time			2		ns
$t_{fs}$ Fail-safe output delay time from input power loss	See <a href="#">图 2</a>		6		$\mu\text{s}$

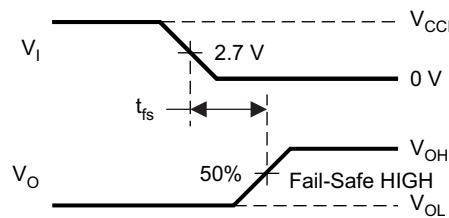
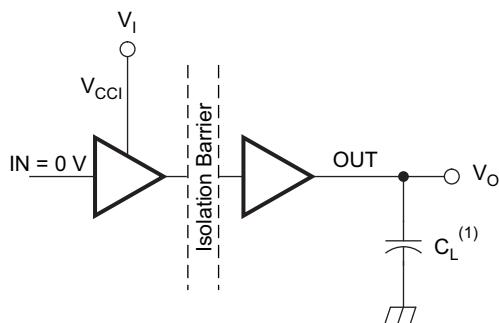
(1) Also known as pulse skew.

## 16 Parameter Measurement Information



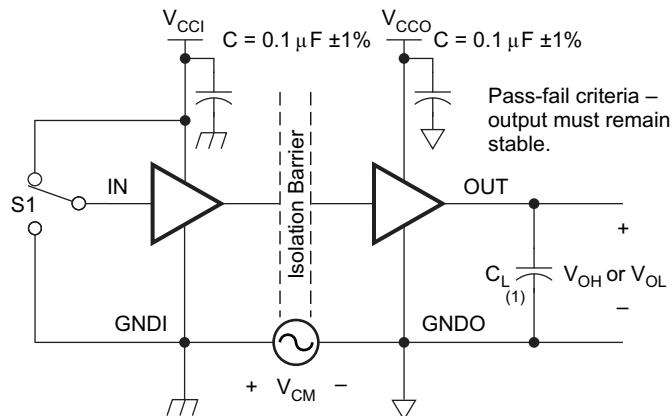
- A. The input pulse is supplied by a generator having the following characteristics: PRR  $\leq$  50 kHz, 50% duty cycle,  $t_r \leq 3\text{ns}$ ,  $t_f \leq 3\text{ns}$ ,  $Z_O = 50\Omega$ .
- B.  $C_L = 15\text{ pF}$  and includes instrumentation and fixture capacitance within  $\pm 20\%$ .

**图 1. Switching Characteristic Test Circuit and Voltage Waveforms**



- A.  $C_L = 15\text{ pF}$  and includes instrumentation and fixture capacitance within  $\pm 20\%$ .

**图 2. Failsafe Delay Time Test Circuit and Voltage Waveforms**



- A.  $C_L = 15\text{ pF}$  and includes instrumentation and fixture capacitance within  $\pm 20\%$ .

**图 3. Common-Mode Transient Immunity Test Circuit**

## 17 Device Information

### 17.1 Package Characteristics

over recommended operating conditions (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
L(I01) Minimum air gap (Clearance)	Shortest terminal to terminal distance through air	7.6			mm
L(I02) Minimum external tracking (Creepage)	Shortest terminal to terminal distance across the package surface	7.6			mm
CTI Tracking resistance (Comparative Tracking Index)	DIN EN 60112 (VDE 0303-11)	≥400			V
Minimum internal gap (Internal Clearance)	Distance through the insulation	0.014			mm
R <sub>IO</sub> Isolation resistance, input to output <sup>(1)</sup>	Input to output, V <sub>IO</sub> = 500 V, all pins on each side of the barrier tied together creating a two-terminal device		>10 <sup>12</sup>		Ω
C <sub>IO</sub> Barrier capacitance input to output <sup>(1)</sup>	V <sub>IO</sub> = 0.4 sin(2πft), f = 1 MHz		2		pF
C <sub>I</sub> Input capacitance to ground <sup>(2)</sup>	V <sub>I</sub> = V <sub>CC</sub> /2 + 0.4 sin(2πft), f = 1 MHz, V <sub>CC</sub> = 5 V		2		pF

(1) All pins on each side of the barrier tied together creating a two-terminal device.

(2) Measured from input pin to ground.

### 注

Creepage and clearance requirements should be applied according to the specific equipment isolation standards of an application. Care should be taken to maintain the creepage and clearance distance of a board design to ensure that the mounting pads of the isolator on the printed circuit board do not reduce this distance.

Creepage and clearance on a printed circuit board become equal according to the measurement techniques shown in the Isolation Glossary. Techniques such as inserting grooves and/or ribs on a printed circuit board are used to help increase these specifications.

### 17.2 IEC 60664-1 Ratings Table

PARAMETER	TEST CONDITIONS	SPECIFICATION
Basic Isolation Group	Material Group	II
Installation Classification	Rated mains voltages <= 150 Vrms	I - IV
	Rated mains voltages <= 300 Vrms	I - IV
	Rated mains voltages <= 400 Vrms	I - III

## 17.3 Insulation Characteristics

over recommended operating conditions (unless otherwise noted)

<b>PARAMETER</b>		<b>TEST CONDITIONS</b>	<b>SPECIFICATION</b>	<b>UNIT</b>
$V_{IORM}$	Maximum working insulation voltage		1414	Vpeak
$V_{PR}$	Input to output test voltage	Method a, After environmental tests subgroup 1, $V_{PR} = V_{IORM} \times 1.6$ , $t = 10$ s, Partial discharge < 5 pC	2262	Vpeak
		After Input/Output Safety Test Subgroup 2/3, $V_{PR} = V_{IORM} \times 1.2$ , $t = 10$ s, Partial discharge < 5 pC	1697	
		Method b1, $V_{PR} = V_{IORM} \times 1.875$ , $t = 1$ s (100% Production test) Partial discharge < 5 pC	2651	
$V_{IOTM}$	Transient overvoltage	$t = 60$ sec (qualification)	4242	Vpeak
$V_{ISO}$	Isolation voltage per UL	$V_{TEST} = V_{ISO}$ , $t = 60$ sec (qualification)	2500	Vrms
		$V_{TEST} = 1.2 \times V_{ISO}$ , $t = 1$ sec (100% production)	3000	
$R_s$	Insulation resistance	$V_{TEST} = 500$ V at $T_S = 150^\circ\text{C}$	>10 <sup>9</sup>	$\Omega$
	Pollution degree		2	

## 17.4 Regulatory Information

<b>VDE</b>	<b>CSA</b>	<b>UL</b>
Certified according to DIN VDE V 0884-11:2017-01	Approved according to IEC 60950-1 and IEC 61010-1	Recognized under UL 1577 Component Recognition Program
Certificate Number: 40047657	Master Contract Number: 220991	File Number: E181974

## 17.5 IEC Safety Limiting Values

Safety limiting intends to prevent potential damage to the isolation barrier upon failure of input or output circuitry. A failure of the IO can allow low resistance to ground or the supply and, without current limiting, dissipate sufficient power to overheat the die and damage the isolation barrier potentially leading to secondary system failures.

<b>PARAMETER</b>		<b>TEST CONDITIONS</b>	<b>MIN</b>	<b>TYP</b>	<b>MAX</b>	<b>UNIT</b>
Is	Safety input, output, or supply current	$\theta_{JA} = 212^\circ\text{C/W}$ , $V_I = 5.5$ V, $T_J = 170^\circ\text{C}$ , $T_A = 25^\circ\text{C}$			112	mA
		$\theta_{JA} = 212^\circ\text{C/W}$ , $V_I = 3.6$ V, $T_J = 170^\circ\text{C}$ , $T_A = 25^\circ\text{C}$			171	
Ts	Maximum Case Temperature				150	°C

The safety-limiting constraint is the absolute maximum junction temperature specified in the absolute maximum ratings table. The power dissipation and junction-to-air thermal impedance of the device installed in the application hardware determines the junction temperature. The assumed junction-to-air thermal resistance in the Thermal Characteristics table is that of a device installed on a High-K Test Board for Leaded Surface Mount Packages. The power is the recommended maximum input voltage times the current. The junction temperature is then the ambient temperature plus the power times the junction-to-air thermal resistance.

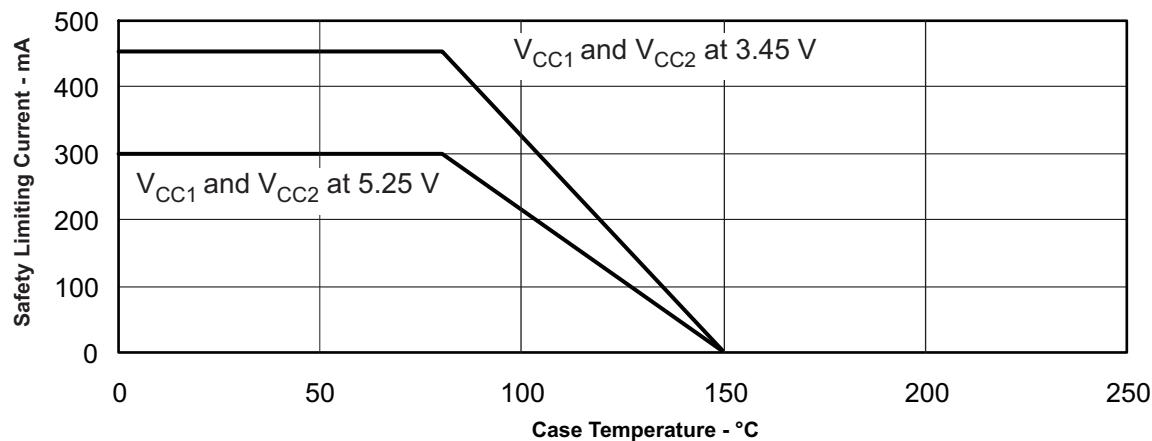


图 4. DW-16 Theta-JC Thermal Derating Curve per IEC 60747-5-2

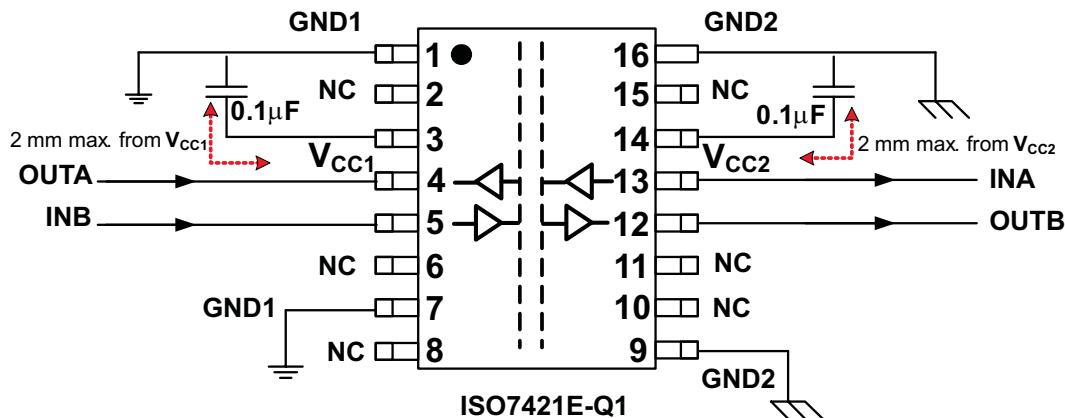


图 5. Typical ISO7421E-Q1 Application Circuit

## 17.6 Equivalent Input And Output Schematic Diagrams

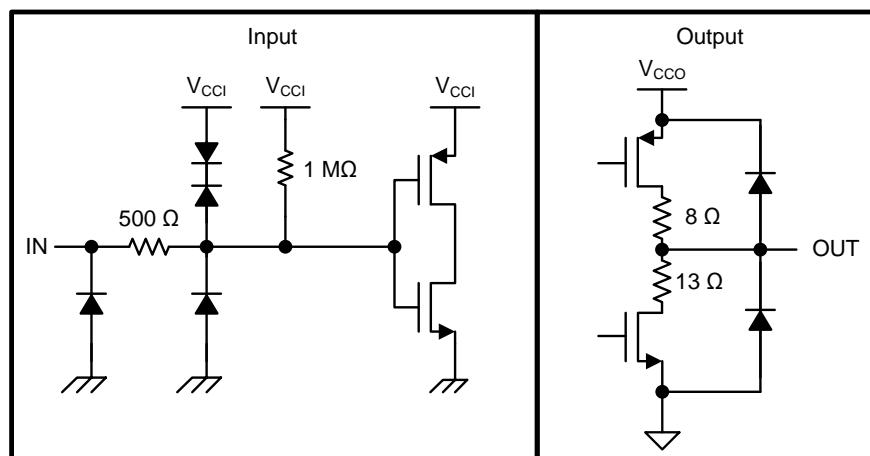
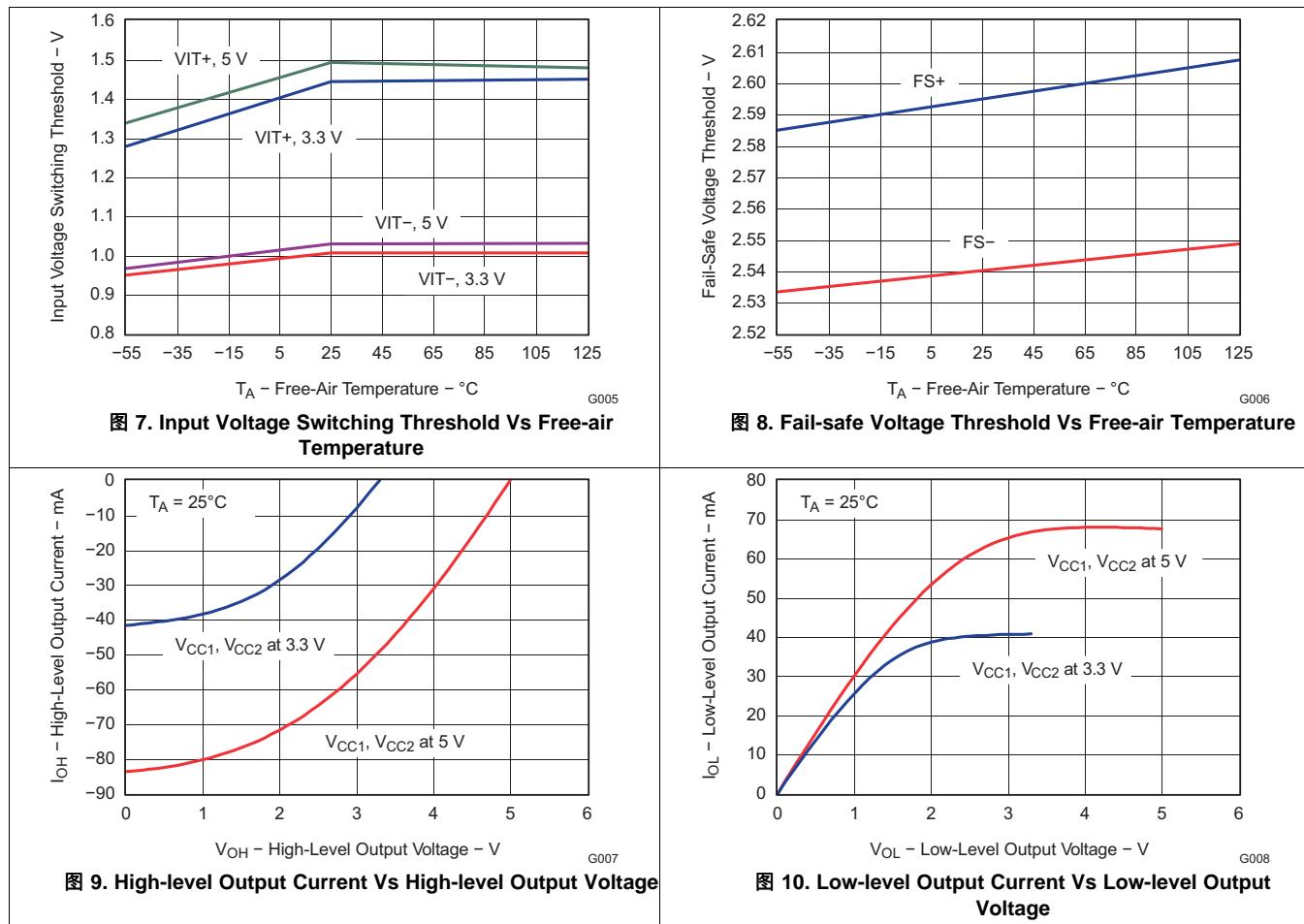


图 6. I/O Schematic

## 18 Typical Characteristics



## 19 Revision History

注：之前版本的页码可能与当前版本有所不同。

### Changes from Revision B (May 2012) to Revision C

**Page**

• 删除了特性项目符号“宽环境温度：−40°C 至 125°C”，因为涉及重复 .....	1
• 将特性项目符号从“符合 VDE 标准的 4kV 峰值最大隔离，符合 UL 1577 标准的 2.5kVrms 隔离，通过 IEC 60950-1 和 IEC 61010-1 终端设备标准验证的 CSA。所有审批待定。”更改为“符合 VDE 标准的 4242V <sub>PK</sub> 隔离，符合 UL 1577 标准的 2.5kVrms 隔离，通过 IEC 60950-1 和 IEC 61010-1 终端设备标准验证的 CSA” .....	1
• 将“ISO7421E-Q1 可提供双通道电隔离...”更改为“ISO7421E-Q1 可提供电隔离...”，改动位置在说明部分 .....	1
• 添加了器件的简化原理图 .....	1
• Changed column titles From:"INPUT SIDE (VCC)" To:"INPUT SIDE V <sub>CC</sub> (V <sub>CC1</sub> )" and From:"OUTPUT SIDE (VCC)" To:"OUTPUT SIDE V <sub>CC</sub> (V <sub>CC2</sub> )" in <a href="#">Device Function Table</a> .....	3
• Changed MAX VALUE for V <sub>I</sub> From: "6 V" To: "V <sub>CC</sub> + 0.5 V" .....	3
• Added : "Maximum voltage must not exceed 6 V. A strongly driven input signal can weakly power the floating V <sub>CC</sub> via an internal protection diode and cause undetermined output." .....	3
• Deleted Supply Current parameters with V <sub>CC1</sub> and V <sub>CC2</sub> at 5 V ± 5% for ISO7420x in <a href="#">Electrical Characteristics</a> table since ISO7420x is not included in the data sheet. .....	5
• Deleted Supply Current parameters with V <sub>CC1</sub> at 5 V ± 5%, V <sub>CC2</sub> at 3.3 V ± 5% for ISO7420x in <a href="#">Electrical Characteristics</a> table since ISO7420x is not included in the data sheet. .....	6
• Deleted Supply Current parameters with V <sub>CC1</sub> at 3.3 V ± 5%, V <sub>CC2</sub> at 5 V ± 5% for ISO7420x in <a href="#">Electrical Characteristics</a> table since ISO7420x is not included in the data sheet. .....	7
• Deleted Supply Current parameters with V <sub>CC1</sub> and V <sub>CC2</sub> at 3.3 V ± 5% for ISO7420x in <a href="#">Electrical Characteristics</a> table since ISO7420x is not included in the data sheet. .....	8
• Changed V <sub>CC1</sub> to V <sub>CC1</sub> and V <sub>CC</sub> /2 to 50% in <a href="#">图 1</a> .....	9
• Changed V <sub>CC1</sub> to V <sub>CC1</sub> and IN From:"0V or V <sub>CC1</sub> " To:"0 V" in <a href="#">图 2</a> .....	9
• Corrected 'Ground' symbols on both sides of the Isolation Barrier in <a href="#">图 3</a> .....	9
• Changed MIN specification for Clearance or L(I01) From: "8.34 mm" To:"7.6 mm" in <a href="#">Package Characteristics</a> table. ....	10
• Changed MIN specification for Creepage or L(I02) From: "8.1 mm" To:"7.6 mm" in <a href="#">Package Characteristics</a> table. ....	10
• Changed CTI TEST CONDITIONS From: " DIN IEC 60112 / VDE 0303 Part 1" To: "DIN EN 60112 (VDE 0303-11)" ....	10
• Added "V <sub>TEST</sub> = 1.2 x V <sub>ISO</sub> " to V <sub>ISO</sub> parameter TEST CONDITIONS in <a href="#">Insulation Characteristics</a> table .....	11
• Changed VDE standard name From: "IEC 60747-5-2" To:"DIN VDE V 0884-11:2017-01" and document reference From:"File Number: Pending" To:"Certificate Number: 40047657" respectively in <a href="#">Regulatory Information</a> table.....	11
• Changed CSA standard reference From:"Approved under CSA Component Acceptance Notice" To:"Approved according to IEC 60950-1 and IEC 61010-1" and document reference From: "File Number: pending" To:"Master Contract Number: 220991" respectively in <a href="#">Regulatory Information</a> table.....	11
• Changed UL standard reference From:"1577" To:"UL 1577" in <a href="#">Regulatory Information</a> table. ....	11
• Changed ground symbol of 'Output' to differentiate it from 'Input' in <a href="#">图 6</a> .....	12

### Changes from Revision A (March 2012) to Revision B

**Page**

• 将信号传输速率信息从 1Mbps 更改为 50Mbps .....	1
• Changed Signaling rate max value from 1 to 50 Mbps, centered 0 in the min column. ....	4
• Replaced Supply Current section with marked up table from commercial datasheet SLLSE45, changed 8.5 max value to 9.1.....	5
• Replaced Supply Current section with marked up table from commercial datasheet SLLSE45, changed 8.5 max value to 9.1 and changed 5.5 max value to 5.8. ....	6
• Replaced Supply Current section with marked up table from commercial datasheet SLLSE45, changed 5.5 max value to 5.8 and changed 8.5 max value to 9.1. ....	7
• Replaced Supply Current section with marked up table from commercial datasheet SLLSE45, changed 5.5 max value to 5.8.....	8

## 重要声明和免责声明

TI 均以“原样”提供技术性及可靠性数据（包括数据表）、设计资源（包括参考设计）、应用或其他设计建议、网络工具、安全信息和其他资源，不保证其中不含任何瑕疵，且不做任何明示或暗示的担保，包括但不限于对适销性、适合某特定用途或不侵犯任何第三方知识产权的暗示担保。

所述资源可供专业开发人员应用TI 产品进行设计使用。您将对以下行为独自承担全部责任：(1) 针对您的应用选择合适的TI 产品；(2) 设计、验证并测试您的应用；(3) 确保您的应用满足相应标准以及任何其他安全、安保或其他要求。所述资源如有变更，恕不另行通知。TI 对您使用所述资源的授权仅限于开发资源所涉及TI 产品的相关应用。除此之外不得复制或展示所述资源，也不提供其它TI 或任何第三方的知识产权授权许可。如因使用所述资源而产生任何索赔、赔偿、成本、损失及债务等，TI 对此概不负责，并且您须赔偿由此对TI 及其代表造成的损害。

TI 所提供产品均受TI 的销售条款 (<http://www.ti.com.cn/zh-cn/legal/termsofsale.html>) 以及ti.com.cn 上或随附TI 产品提供的其他可适用条款的约束。TI 提供所述资源并不扩展或以其他方式更改TI 针对TI 产品所发布的可适用的担保范围或担保免责声明。

邮寄地址：上海市浦东新区世纪大道 1568 号中建大厦 32 楼，邮政编码：200122  
Copyright © 2019 德州仪器半导体技术（上海）有限公司

**PACKAGING INFORMATION**

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
ISO7421EQDWRQ1	ACTIVE	SOIC	DW	16	2000	RoHS & Green	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISO7421EQ	<b>Samples</b>

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

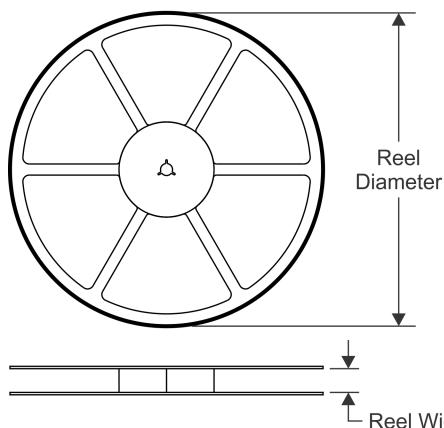
(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

**Important Information and Disclaimer:** The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

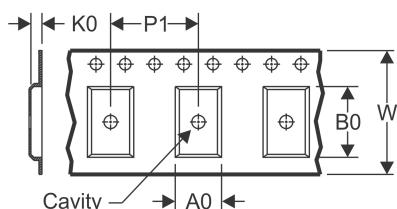
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

## TAPE AND REEL INFORMATION

### REEL DIMENSIONS

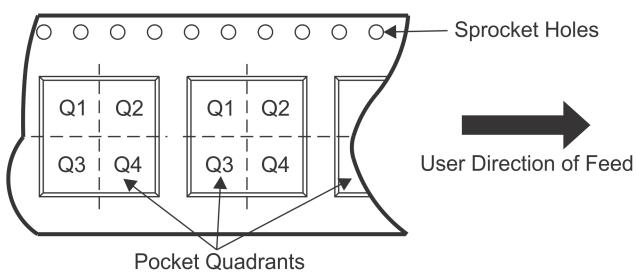


### TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

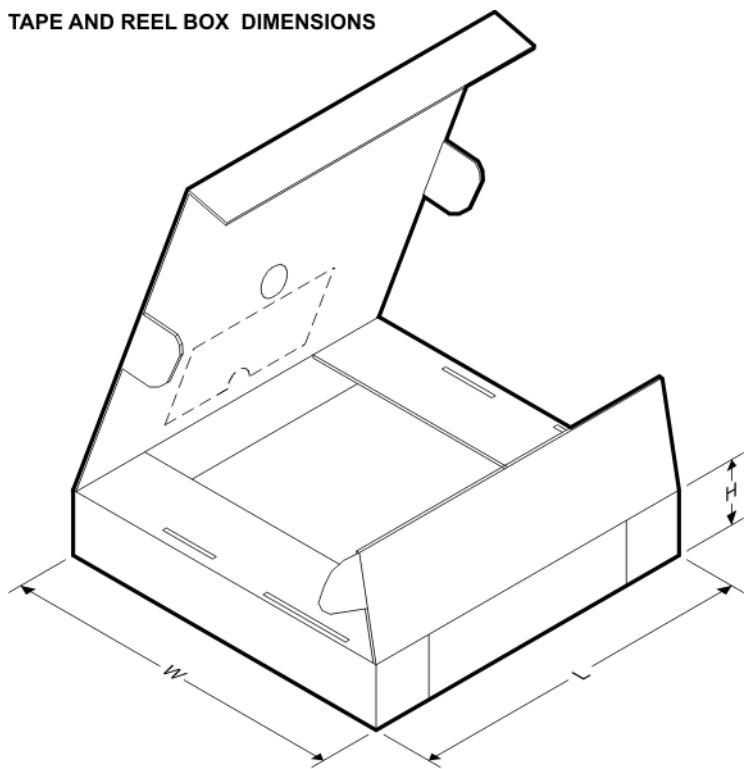
### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
ISO7421EQDWQRQ1	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1

## TAPE AND REEL BOX DIMENSIONS



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
ISO7421EQDWQRQ1	SOIC	DW	16	2000	350.0	350.0	43.0

# GENERIC PACKAGE VIEW

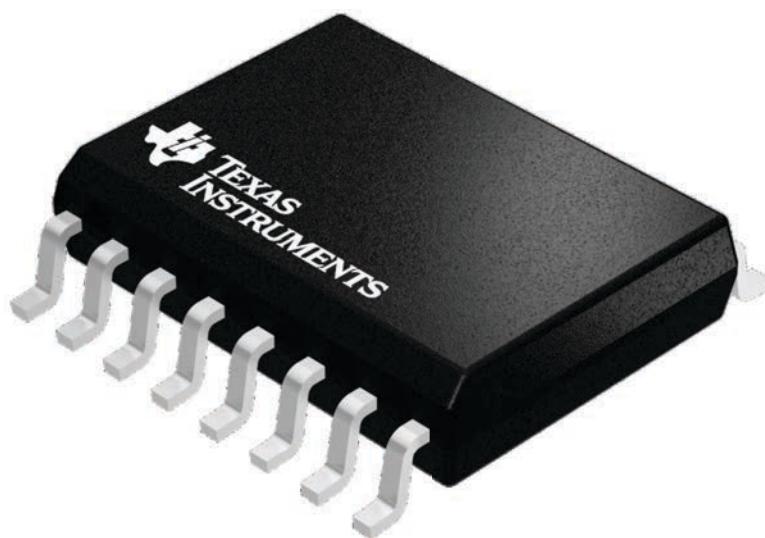
DW 16

SOIC - 2.65 mm max height

7.5 x 10.3, 1.27 mm pitch

SMALL OUTLINE INTEGRATED CIRCUIT

This image is a representation of the package family, actual package may vary.  
Refer to the product data sheet for package details.



4224780/A

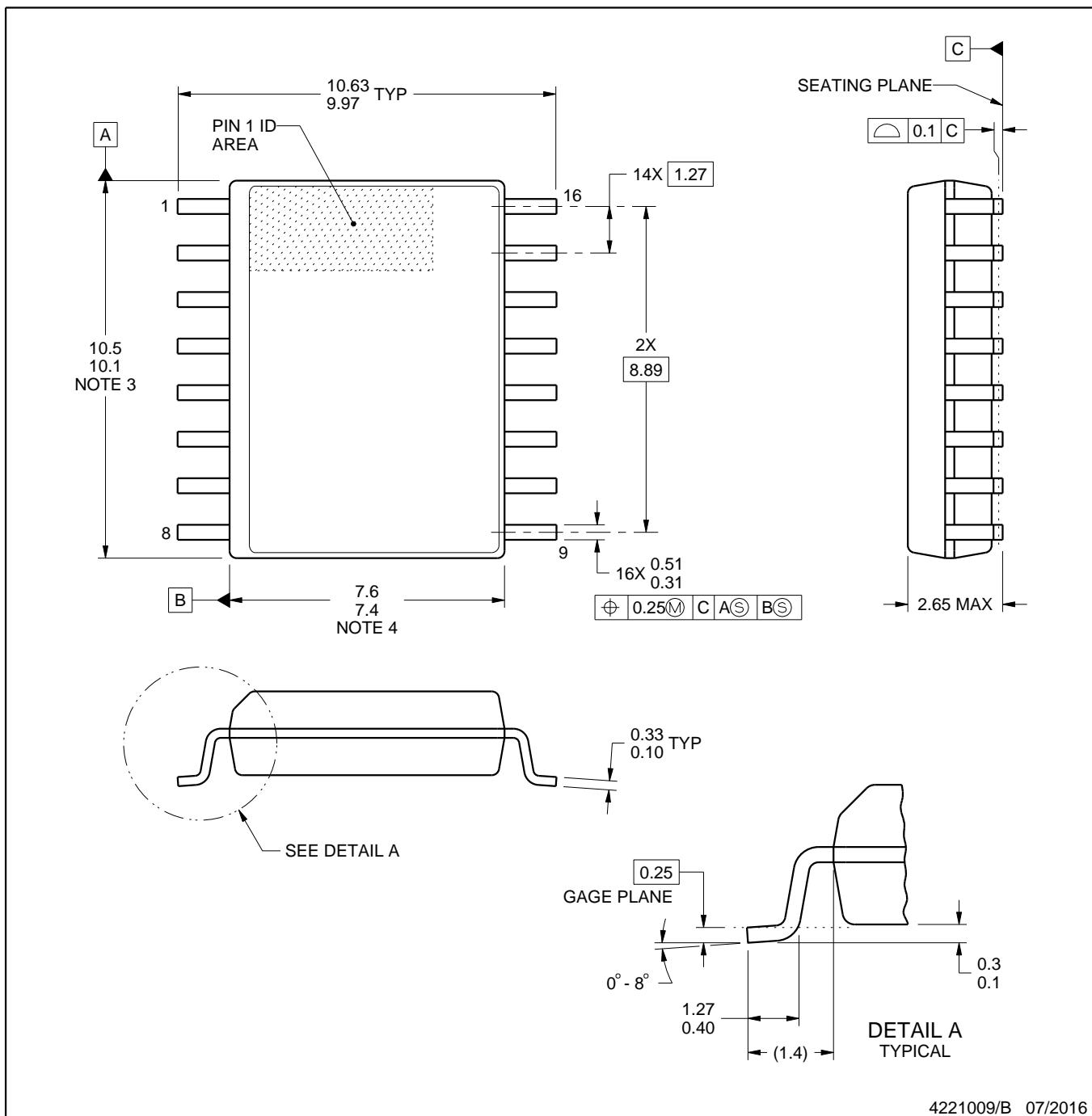
DW0016B



# PACKAGE OUTLINE

SOIC - 2.65 mm max height

SOIC



4221009/B 07/2016

## NOTES:

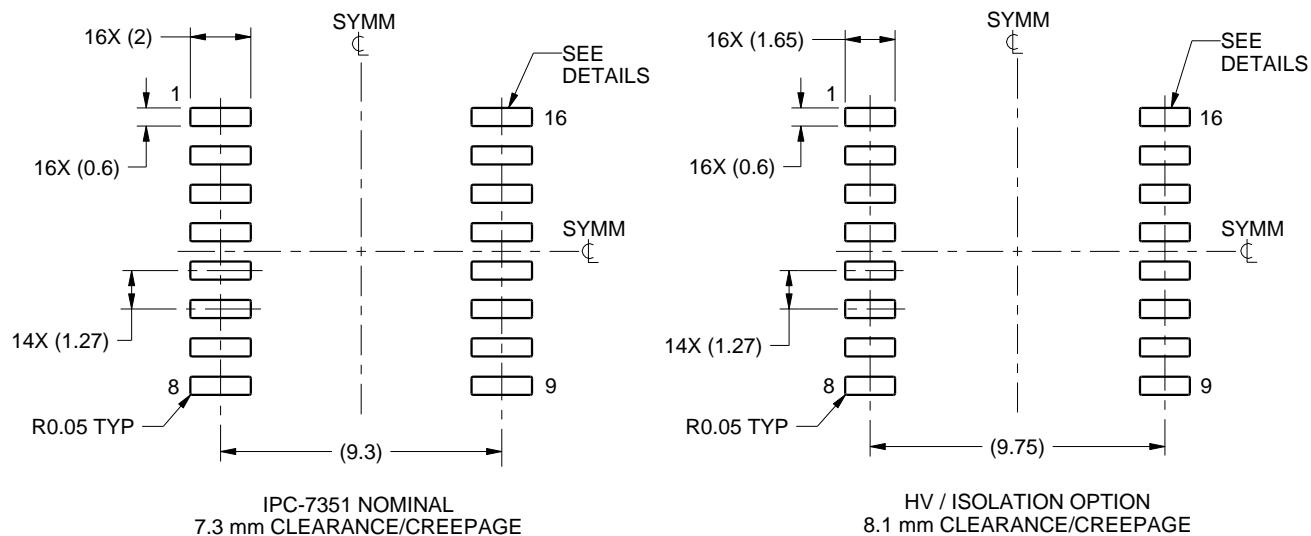
- All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- This drawing is subject to change without notice.
- This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm, per side.
- This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm, per side.
- Reference JEDEC registration MS-013.

# EXAMPLE BOARD LAYOUT

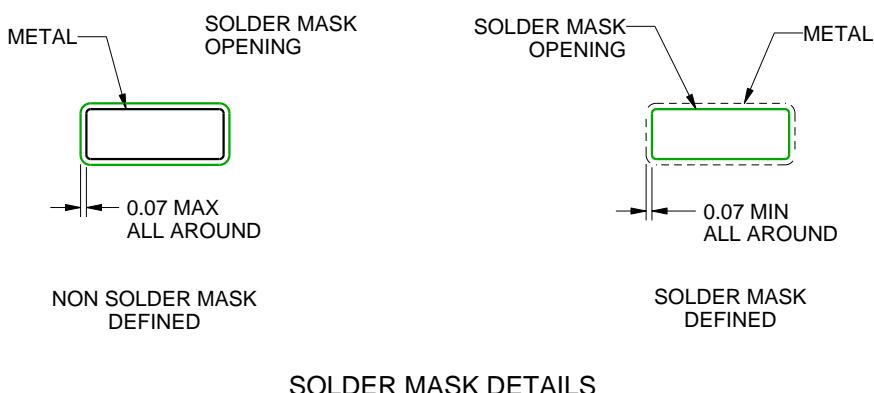
DW0016B

SOIC - 2.65 mm max height

SOIC



LAND PATTERN EXAMPLE  
SCALE:4X



SOLDER MASK DETAILS

4221009/B 07/2016

NOTES: (continued)

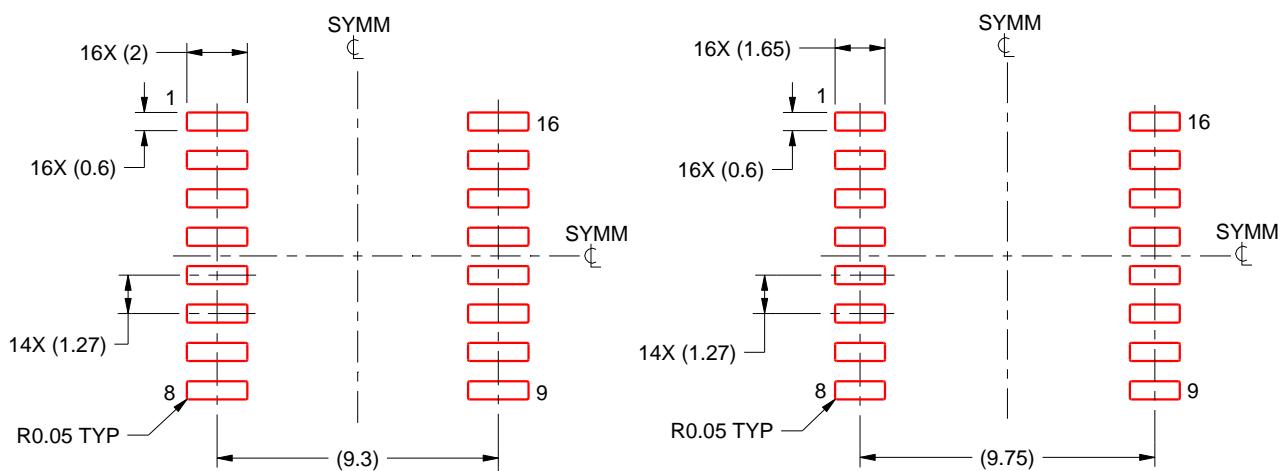
6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

# EXAMPLE STENCIL DESIGN

DW0016B

SOIC - 2.65 mm max height

SOIC



SOLDER PASTE EXAMPLE  
BASED ON 0.125 mm THICK STENCIL  
SCALE:4X

4221009/B 07/2016

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

## 重要声明和免责声明

TI 均以“原样”提供技术性及可靠性数据（包括数据表）、设计资源（包括参考设计）、应用或其他设计建议、网络工具、安全信息和其他资源，不保证其中不含任何瑕疵，且不做任何明示或暗示的担保，包括但不限于对适销性、适合某特定用途或不侵犯任何第三方知识产权的暗示担保。

所述资源可供专业开发人员应用TI 产品进行设计使用。您将对以下行为独自承担全部责任：(1) 针对您的应用选择合适的TI 产品；(2) 设计、验证并测试您的应用；(3) 确保您的应用满足相应标准以及任何其他安全、安保或其他要求。所述资源如有变更，恕不另行通知。TI 对您使用所述资源的授权仅限于开发资源所涉及TI 产品的相关应用。除此之外不得复制或展示所述资源，也不提供其它TI 或任何第三方的知识产权授权许可。如因使用所述资源而产生任何索赔、赔偿、成本、损失及债务等，TI 对此概不负责，并且您须赔偿由此对TI 及其代表造成的损害。

TI 所提供产品均受TI 的销售条款 (<http://www.ti.com.cn/zh-cn/legal/termsofsale.html>) 以及ti.com.cn 上或随附TI 产品提供的其他可适用条款的约束。TI 提供所述资源并不扩展或以其他方式更改TI 针对TI 产品所发布的可适用的担保范围或担保免责声明。

邮寄地址：上海市浦东新区世纪大道 1568 号中建大厦 32 楼，邮政编码：200122  
Copyright © 2020 德州仪器半导体技术（上海）有限公司